

Slides on resonant tunneling

3rd lecture on transport in FFFN35

2018-11-20

Transmission $T(E)$ for double barrier

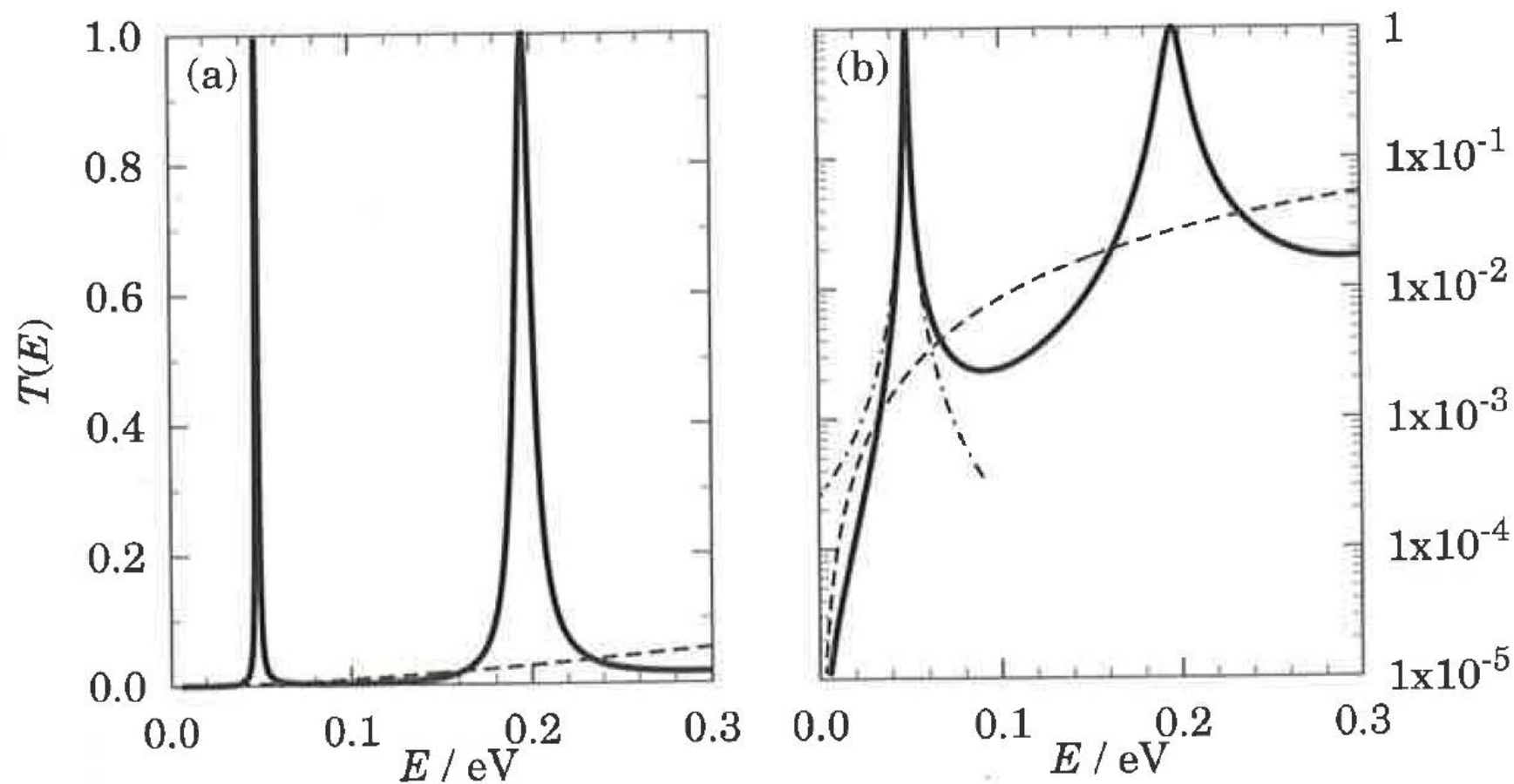
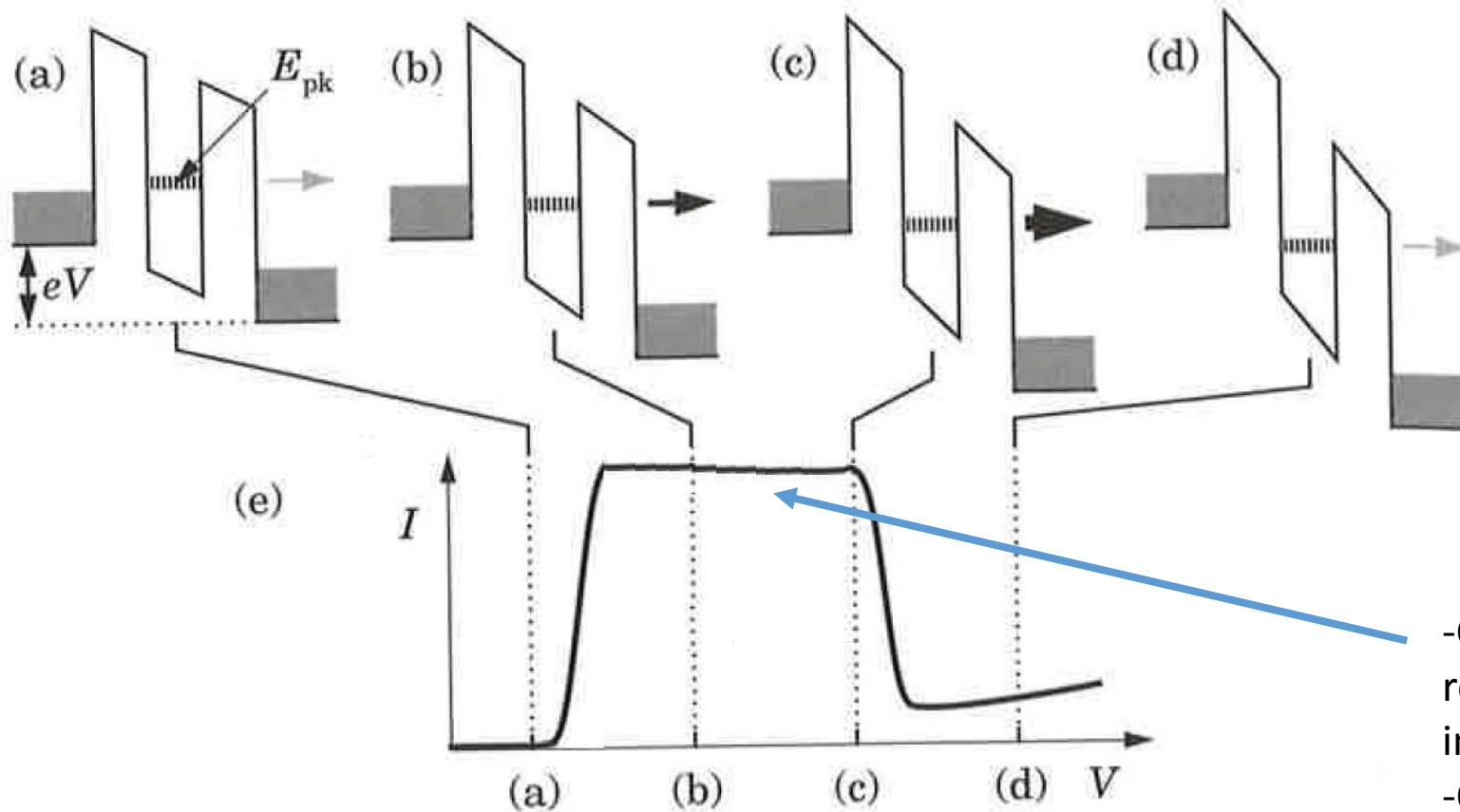


FIGURE 5.11.

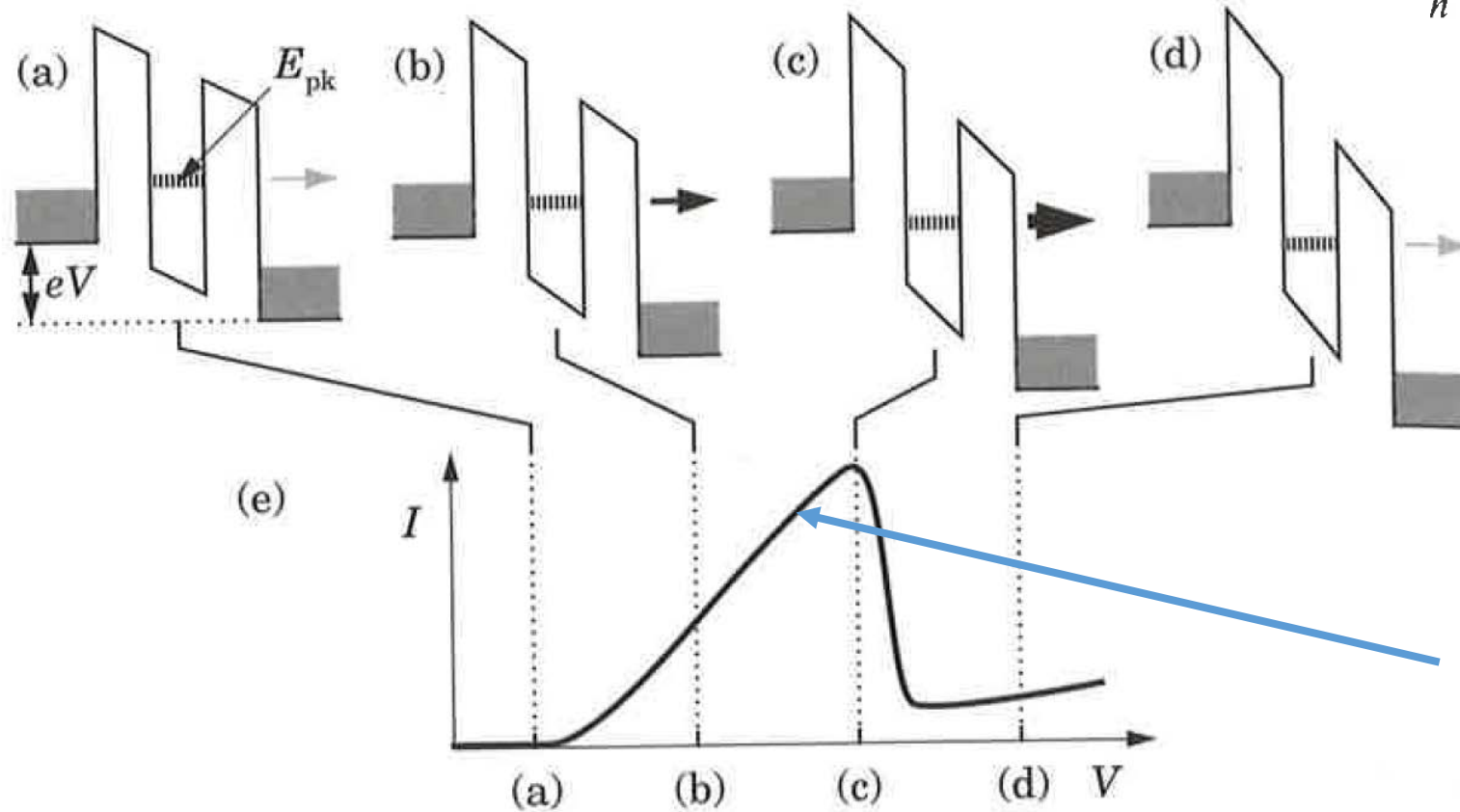
Resonant tunneling, 1D:

$$I = \frac{2e}{h} \int_{\mu_R}^{\mu_L} T(E) dE$$



- Constant current if resonant state is in the bias window.
- Otherwise low current.

Resonant tunneling, 3D:



$$J = \frac{e}{h} \frac{m}{\pi \hbar^2} \int_{U_L}^{\infty} [\Theta(\mu_L - E) - \Theta(\mu_R - E)] T(E) dE$$

$$J = \frac{e}{h} \frac{m}{\pi \hbar^2} \int_{U_L}^{\infty} [\Theta(\mu_L - E_{pk}) - \Theta(\mu_R - E_{pk})] T(E) dE$$

$$J = \frac{e}{h} \frac{m}{\pi \hbar^2} \int_{U_L}^{\infty} eV T(E) dE$$

$T(E)$ large only at E_{pk}

-Linearly increasing current as more ways to choose k_x , k_y and k_z with increasing bias voltage V .
-Otherwise similar to 1D.

FIGURE 5.13.

Resonant tunneling diodes, measured data

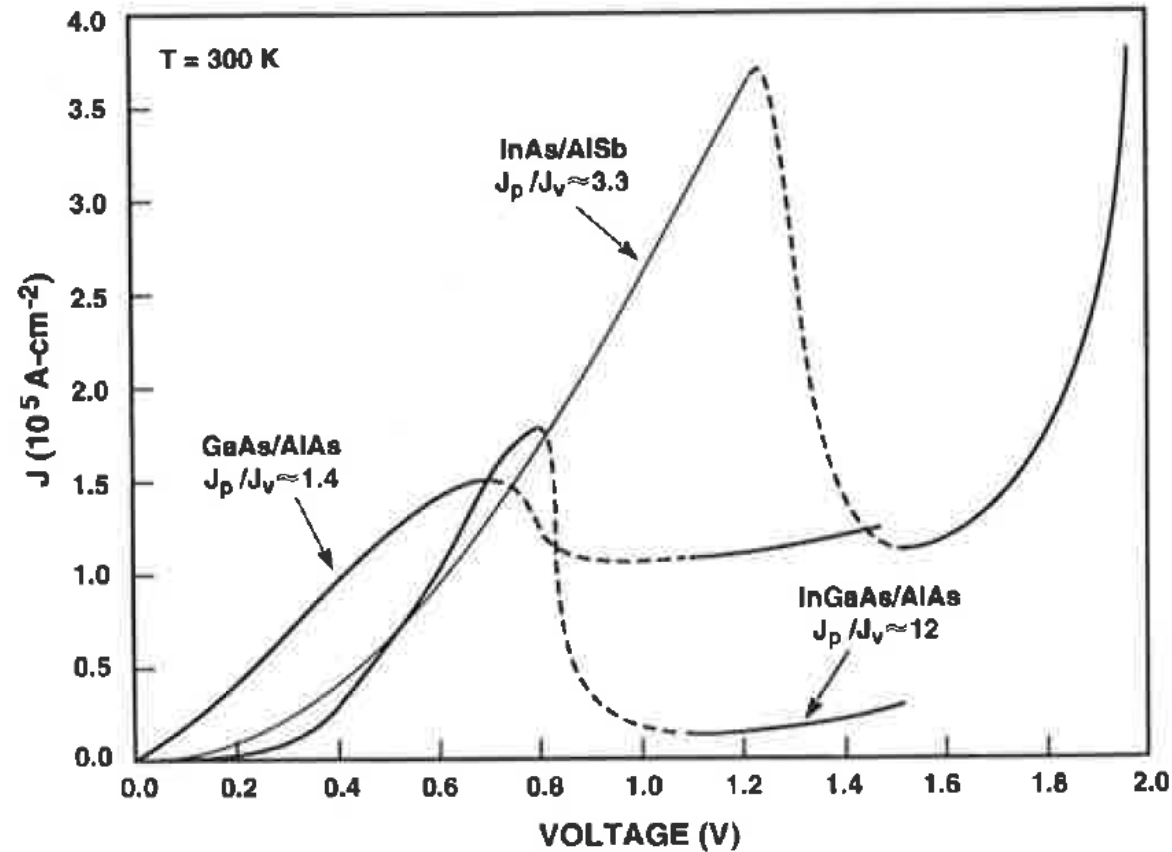


FIGURE 5.15. Characteristics of resonant-tunnelling diodes in three material systems measured at room temperature. [From Brown (1994).]